**Product data sheet** 

## 1. General description

PNP low  $V_{CEsat}$  transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4350T

#### 2. Features and benefits

- Low collector-emitter saturation voltage  $V_{\text{CEsat}}$  and corresponding low  $R_{\text{CEsat}}$
- · High collector current capability
- · High collector current gain
- · Improved efficiency due to reduced heat generation
- AEC-Q101 qualified

## 3. Applications

- · Power management applications
- Low and medium power DC/DC converters
- Supply line switching
- · Battery chargers
- Linear voltage regulation with low voltage drop-out (LDO)

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-50	V
I <sub>C</sub>	collector current		-	-	-2	Α
I <sub>CRM</sub>		$\delta \leq 0.25$ ; Operated under pulsed conditions; $t_p \leq 100 \text{ ms}$	-	-	-3	А
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -2 A; $I_B$ = -200 mA; pulsed; $t_p \le$ 300 µs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	-	90	135	mΩ



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# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	
2	Е	emitter		C 
3	С	collector		В—
			1 2	E sym132
			SOT23	

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package							
	Name	Description	Version					
PBSS5350T	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23					

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code[1]
PBSS5350T	ZD%

[1] % = placeholder for manufacturing site code

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## 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	-50	V
$V_{CEO}$	collector-emitter voltage	open base		-	-50	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-5	V
Ic	collector current			-	-2	А
I <sub>CRM</sub>	repetitive peak collector current	$\delta \le 0.25$ ; Operated under pulsed conditions; $t_p \le 100 \text{ ms}$		-	-3	A
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-5	А
I <sub>B</sub>	base current			-	-0.5	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	300	mW
			[2]	-	480	mW
			[3]	-	540	mW
			[4]	-	500	mW
			[1] [5]	-	1.2	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [5] Operated under pulsed conditions: pulse width tp  $\leq$  100 ms, duty cycle  $\delta \leq$  0.25.

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
uiy-a)	thermal resistance from		[1]	-	-	417	K/W
	junction to ambient		[2]	-	-	260	K/W
			[3]	-	-	230	K/W
			[4]	-	-	250	K/W
			[1] [5]	-	-	104	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	75	-	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- 2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [5] Operated under pulsed conditions: pulse width  $t_p \le 100$  ms; duty cycle  $\delta \le 0.25$

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# 10. Characteristics

### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>(BR)CBO</sub>	collector-base breakdown voltage	$I_C = -100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	-50	-	-	V
V <sub>(BR)CEO</sub>	collector-emitter breakdown voltage	$I_C = -10 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-50	-	-	V
V <sub>(BR)EBO</sub>	emitter-base breakdown voltage (collector open)	$I_E = -100 \mu A; I_C = 0 A; T_{amb} = 25 °C$	-6	-	-	V
I <sub>СВО</sub>	collector-base cut-off	V <sub>CB</sub> = -50 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
current	current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}; T_j = 150 \text{ °C}$	-	-	-50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -2 V; $I_{C}$ = -100 mA; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	200	-	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -500 mA; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	200	-	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -1 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	200	-	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -2 A; pulsed; $t_{p} \le$ 300 µs; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	130	-	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -3 A; pulsed; $t_{p} \le$ 300 µs; $T_{amb}$ = 25 °C	80	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = -500 mA; $I_B$ = -50 mA; pulsed; $t_p \le$ 300 μs; δ = 0.02; $T_{amb}$ = 25 °C	-	-	-90	mV
		$I_C$ = -1 A; $I_B$ = -50 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-180	mV
		$I_C$ = -2 A; $I_B$ = -100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-320	mV
		$I_C$ = -2 A; $I_B$ = -200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-270	mV
		$I_C$ = -3 A; $I_B$ = -300 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-390	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -2 A; $I_B$ = -200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	90	135	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C$ = -2 A; $I_B$ = -100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-1.1	V
		$I_C$ = -3 A; $I_B$ = -300 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-1.2	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE}$ = -2 V; $I_{C}$ = -1 A; pulsed; $t_{p} \le$ 300 µs; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	-	-1.2	V
f <sub>T</sub>	transition frequency	$V_{CE}$ = -5 V; $I_{C}$ = -100 mA; f = 100 MHz; $T_{amb}$ = 25 °C	100	-	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	-	35	pF

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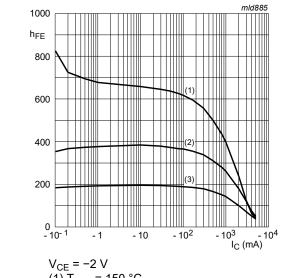
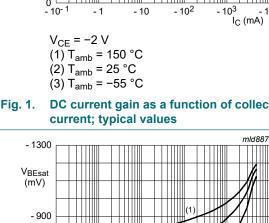


Fig. 1. DC current gain as a function of collector



 $I_C/I_B = 10$ 

- 500

- 100 \_\_\_\_ - 10<sup>- 1</sup>

(1)  $T_{amb} = -55 \, ^{\circ}C$ 

(2) T<sub>amb</sub> = 25 °C (3)  $T_{amb} = 150 \, ^{\circ}C$ 

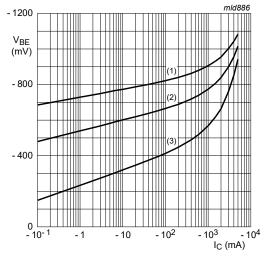
Fig. 3. Base-emitter saturation voltage as a function of Fig. 4. collector current; typical values

- 10

- 10<sup>2</sup>

- 10<sup>4</sup> I<sub>C</sub> (mA)

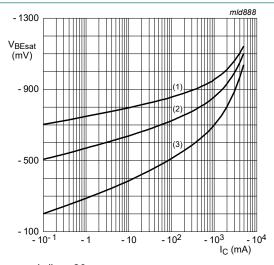
- 10<sup>3</sup>



 $V_{CE} = -2 V$ (1)  $T_{amb} = -55 °C$ (2)  $T_{amb} = 25 °C$ 

(3) T<sub>amb</sub> = 150 °C

Fig. 2. Base-emitter voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B}=20$ 

(1)  $T_{amb} = -55 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb}$  = 150 °C

Base-emitter saturation voltage as a function of collector current; typical values

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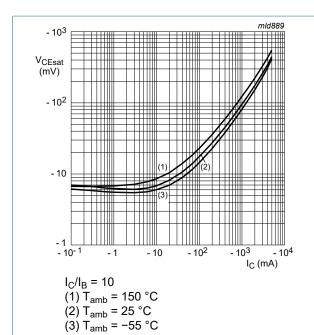


Fig. 5. Collector-emitter saturation voltage as a function of collector current; typical values

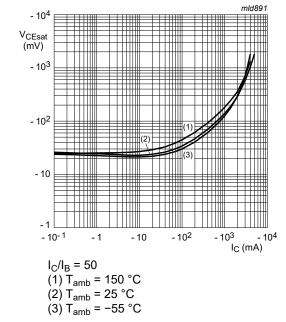


Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values

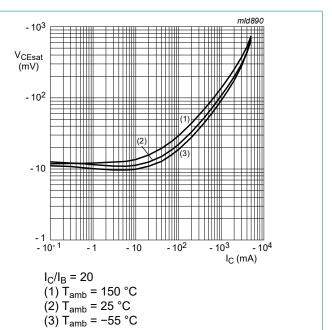
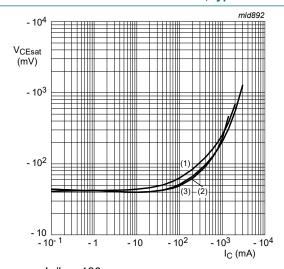


Fig. 6. Collector-emitter saturation voltage as a function of collector current; typical values

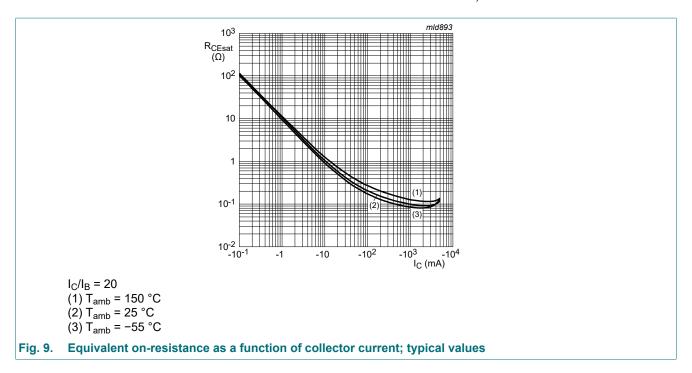


 $I_C/I_B = 100$ (1)  $T_{amb} = 150 \,^{\circ}C$ (2)  $T_{amb} = 25 \,^{\circ}C$ 

(3)  $T_{amb} = -55 \,^{\circ}C$ 

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

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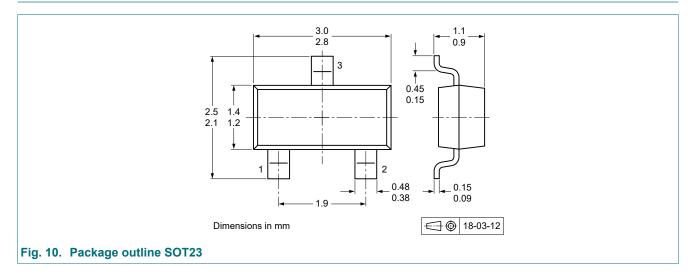


### 11. Test information

#### **Quality information**

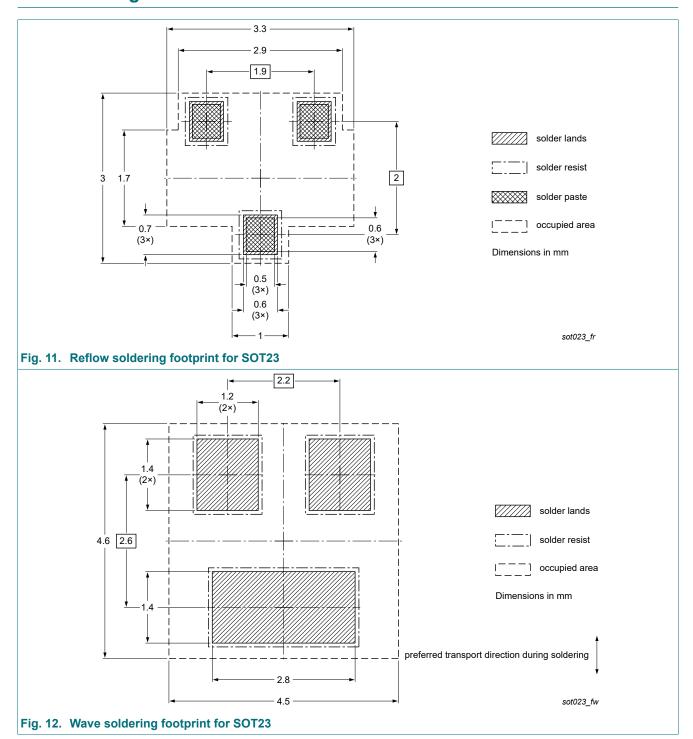
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## 12. Package outline



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# 13. Soldering



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### 50 V, 3 A PNP low VCEsat transistor

# 14. Revision history

#### **Table 8. Revision history**

Table of Novicion motory								
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PBSS5350T v.3	20220510	Product data sheet	-	PBSS5350T v.2				
Modifications:	Nexperia.	<ul> <li>The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> </ul>						
PBSS5350T v.2	20040113	Product data sheet	-	PBSS5350T v.1				
PBSS5350T v.1	20020808	Product data sheet	-	-				

#### 50 V, 3 A PNP low VCEsat transistor

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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PBSS5350T

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For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 10 May 2022

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